

Title (en)

NONVOLATILE SEMICONDUCTOR MEMORY INCLUDING MEANS FOR DETECTING COMPLETION OF WRITING OPERATION

Publication

EP 0255963 B1 19930310 (EN)

Application

EP 87111480 A 19870807

Priority

JP 18631386 A 19860808

Abstract (en)

[origin: EP0255963A2] A semiconductor memory includes memory transistors each having a floating gate is disclosed. This memory is equipped with a detection circuit for detecting a change in the threshold voltage of a selected memory transistor caused by the application of a programming voltage thereto and means responsive to an output of the detection circuit for stopping the application of the programming voltage to the selected memory transistor. A power consumption is thereby reduced in a data writing mode.

IPC 1-7

G11C 16/04; G11C 16/06

IPC 8 full level

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CPC (source: EP US)

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Cited by

EP0513607A3; EP0429720A1; FR2769747A1; US6128222A; DE3925153A1; US5262984A; FR2826496A1; EP1278199A3; EP1278201A3; FR2761191A1; US5953253A; EP0701259A3; EP1531493A3; US6934192B2

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